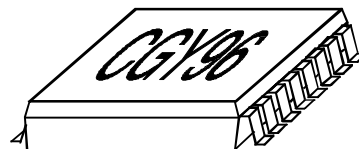


Preliminary Datasheet

- *Power amplifier for GSM class 4 phones
- *3.2 W (35dBm) output power at 3.5 V
- *Overall power added efficiency 50 %
- *Fully integrated 3 stage amplifier
- *Single supply operation
- *Power ramp control
- *Input matched to 50 ohms, simple output match



ESD: **E**lectrostatic **d**ischarge sensitive device,
observe handling precautions!

Type	Marking	Ordering code (taped)	Package
CGY 96	CGY 96	tbd	MW 16

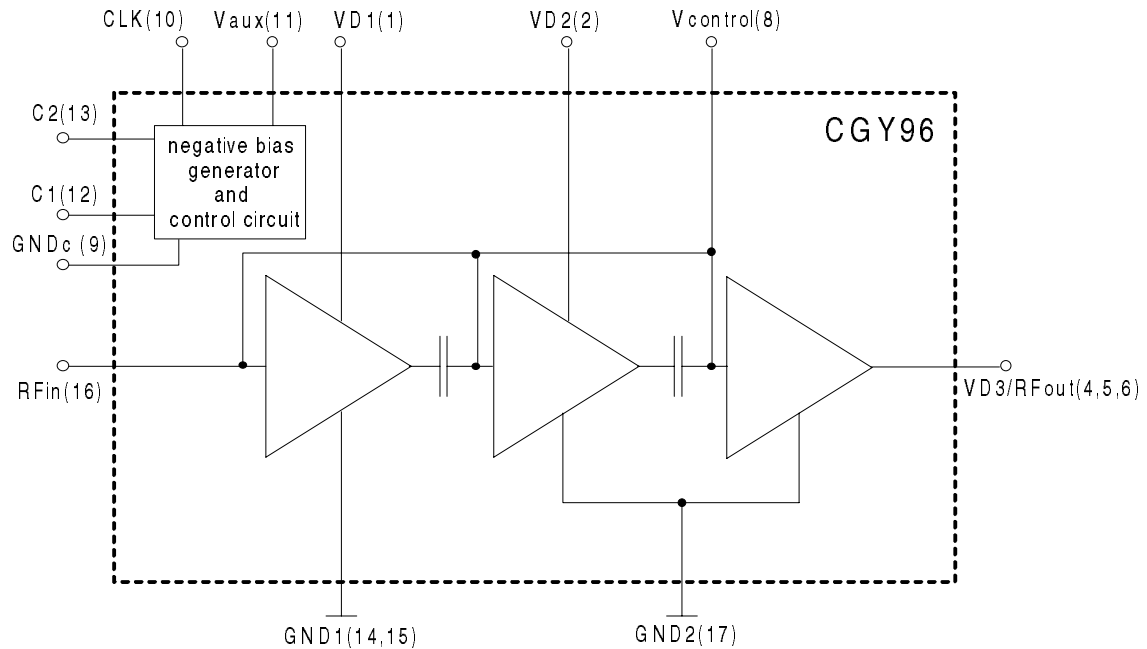
Maximum ratings

Characteristics	Symbol	max. Value	Unit
Positive supply voltage	V_D	9	V
Supply current	I_D	4	A
Channel temperature	T_{Ch}	150	°C
Storage temperature	T_{stg}	-55...+150	°C
Pulse peak power dissipation <i>duty cycle 12.5%, $t_{on}=0.577ms$</i>	P_{Pulse}	tbd	W
Total power dissipation ($T_s \leq 80\text{ °C}$) <i>T_s: Temperature at soldering point</i>	P_{tot}	tbd	W

Thermal Resistance

Channel-soldering point	R_{thChS}	tbd	K/W
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Functional block diagramm:



Pin #		Configuration
1	VD1	Drain voltage 1st stage
2	VD2	Drain voltage 2nd stage
3	n.c.	-
4,5,6	VD3 / RFout	Drain 3rd stage and rf-output
7	n.c.	-
8	Vcontrol	Control voltage for power ramping
9	GNDc	Ground negative voltage generator
10	Clk	Clock input
11	Vaux	Supply voltage neegative voltage generator
12	C1	Coupling capacitor negative voltage generator
13	C2	Block capacitor negativ voltage generator
14,15	Gnd1	Ground pin 1st stage
16	RFIn	RF Input
(17)	GND2	Ground (backside of MW16 housing)

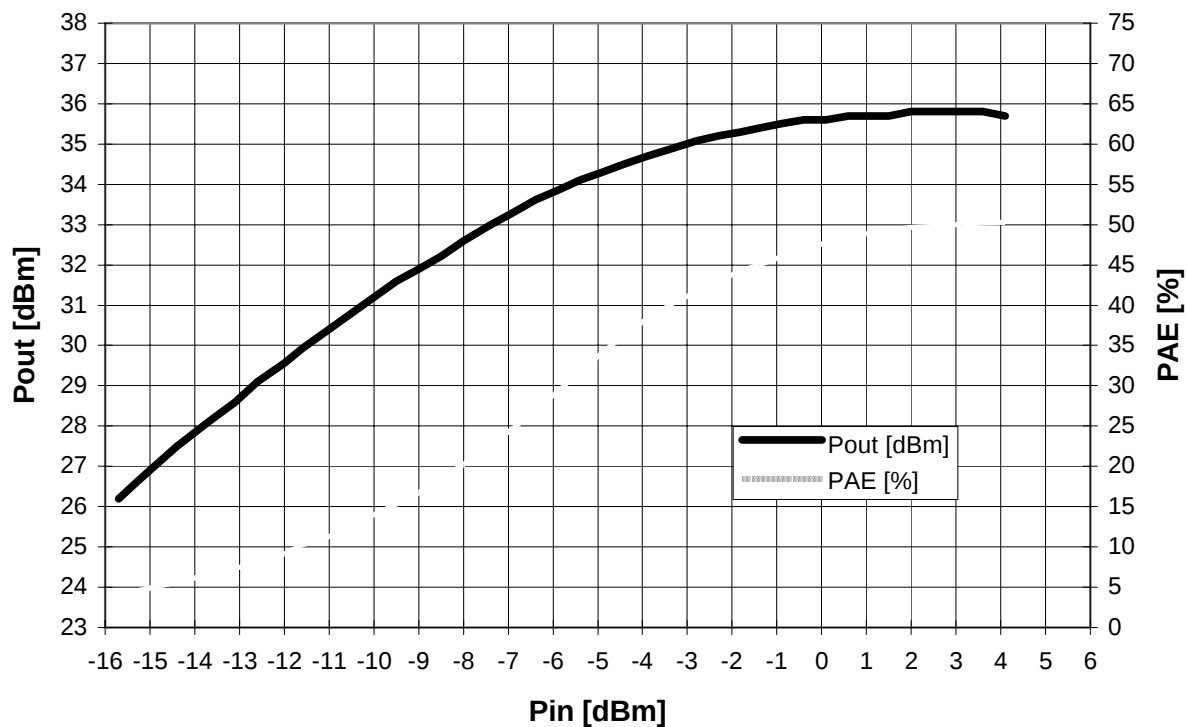
Electrical characteristics

($T_A = 25^\circ\text{C}$, $f=0.9\text{ GHz}$, $Z_S=Z_L=50\text{ Ohm}$, $V_D=3.5\text{V}$, $V_{aux}=3.5\text{V}$, $V_{control}=2.2\text{V}$;
pulsed with a duty cycle of 12.5%, $t_{on}=577\mu\text{sec}$)

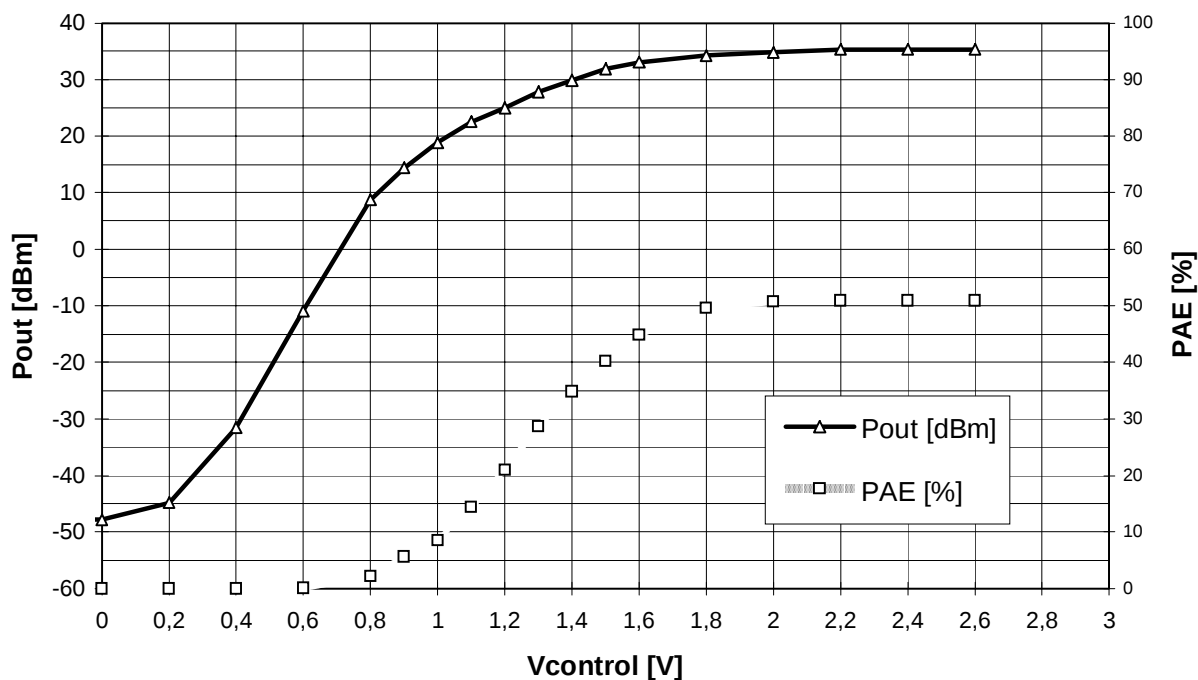
Characteristics	Symbol	min	typ	max	Unit
Supply current <i>Pin=0dBm</i>	I_D	-	2.0	-	A
Supply current neg. voltage gener. <i>Vaux=3.5V</i>	I_{AUX}	-	10	-	mA
Gain (small signal)	G	-	40	-	dB
Power gain <i>P_{in}=0dBm</i>	G_P	-	35	-	dB
Output Power <i>P_{in}=0dBm</i>	P_{OUT}	-	35	-	dBm
Overall Power added Efficiency <i>P_{in}=0dBm</i>	η	-	50	-	%
Dynamic range output power <i>Vcontrol = 0.2...2.2V</i>		-	80	-	dB
Harmonics <i>Pin=0dBm</i>	$H(2f_0)$	-	-40	-	dBc
	$H(3f_0)$	-	-43	-	dBc
	$H(4f_0)$	-	-44	-	dBc
Noise Power in RX (935-960MHz) <i>Pin=0dBm, Pout=35dBm, 100kHz RBW</i>	N_{RX}	-	-81	-	dBm
Stability <i>all spurious outputs < -60dBc, VSWR load, all phase angles</i>		-	10 : 1	-	-
Input VSWR		-	1.7 : 1	-	-

Output Power and PAE vs. Input Power

($V_d=3.5V$, $V_{control}=2.2V$, $f=900MHz$, duty cycle 12.5%, $t_{on}=577\mu s$)

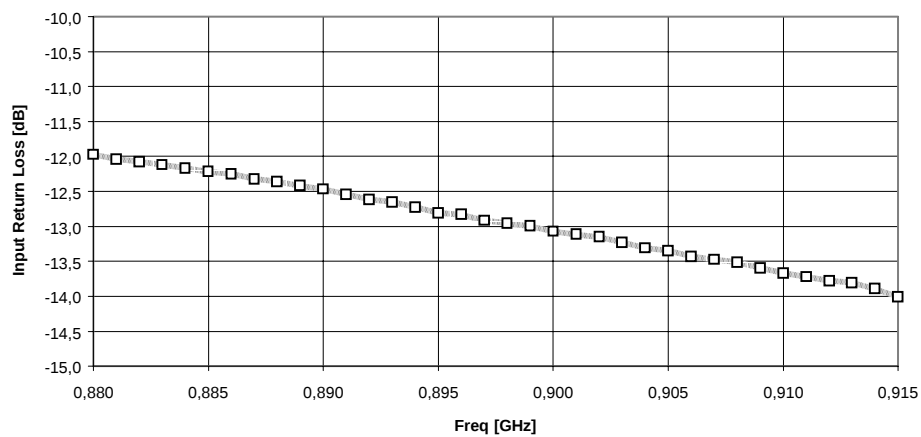
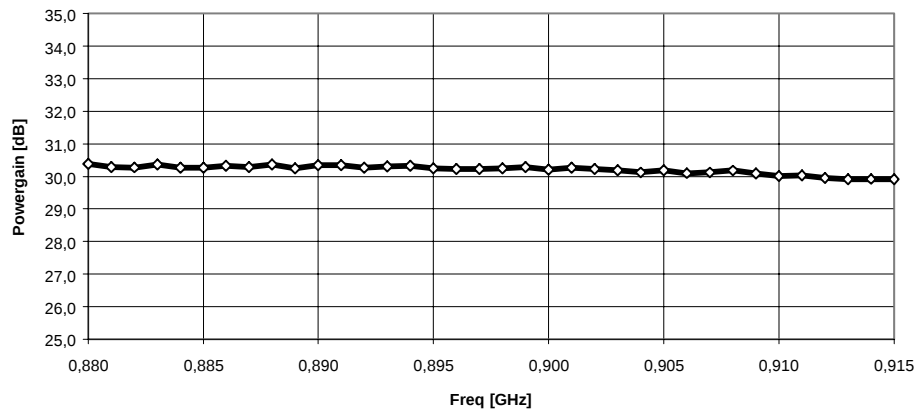
**Output Power and PAE vs. Control Voltage:**

($V_d=3.5V$, $P_{in}=0dBm$, $f=900MHz$, duty cycle 12.5%, $t_{on}=577\mu s$)

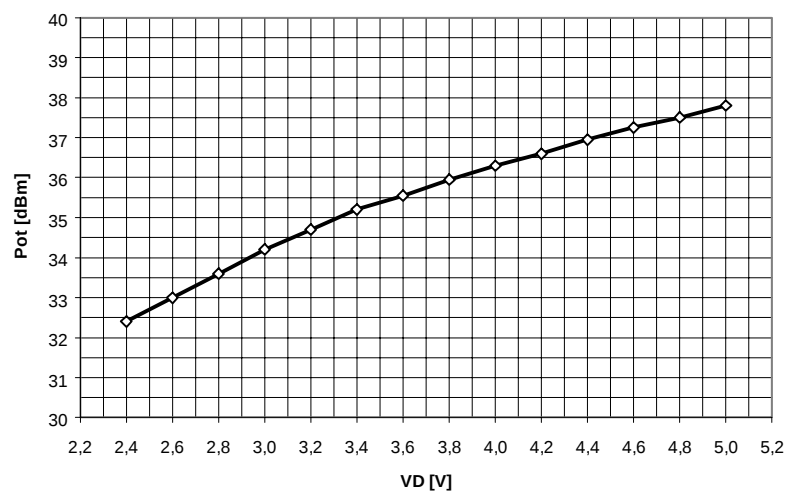


Power Gain and Input Return Loss vs. Frequency

($V_d=3.5V$, $V_{control}=2.2V$, $P_{in}=5dBm$, duty cycle 12.5%, $t_{on}=577\mu s$)

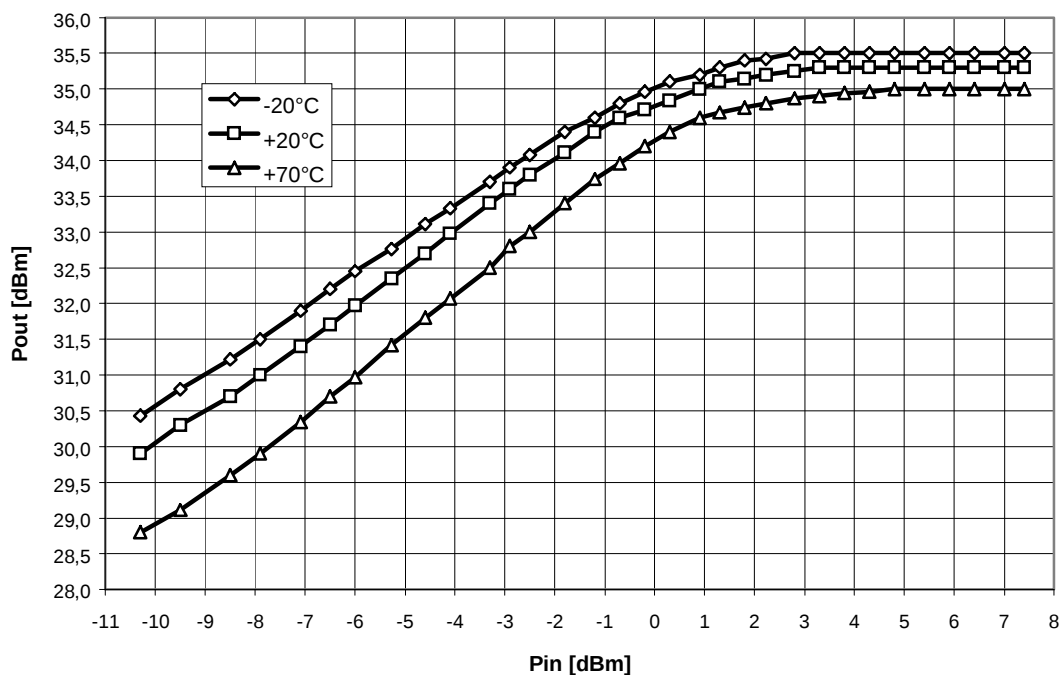
**Output Power vs. Drain Voltage**

(matched for $V_D=3.5V$, $V_{control}=2.2V$, $P_{in}=0dBm$, duty cycle 12.5%, $t_{on}=577\mu s$)



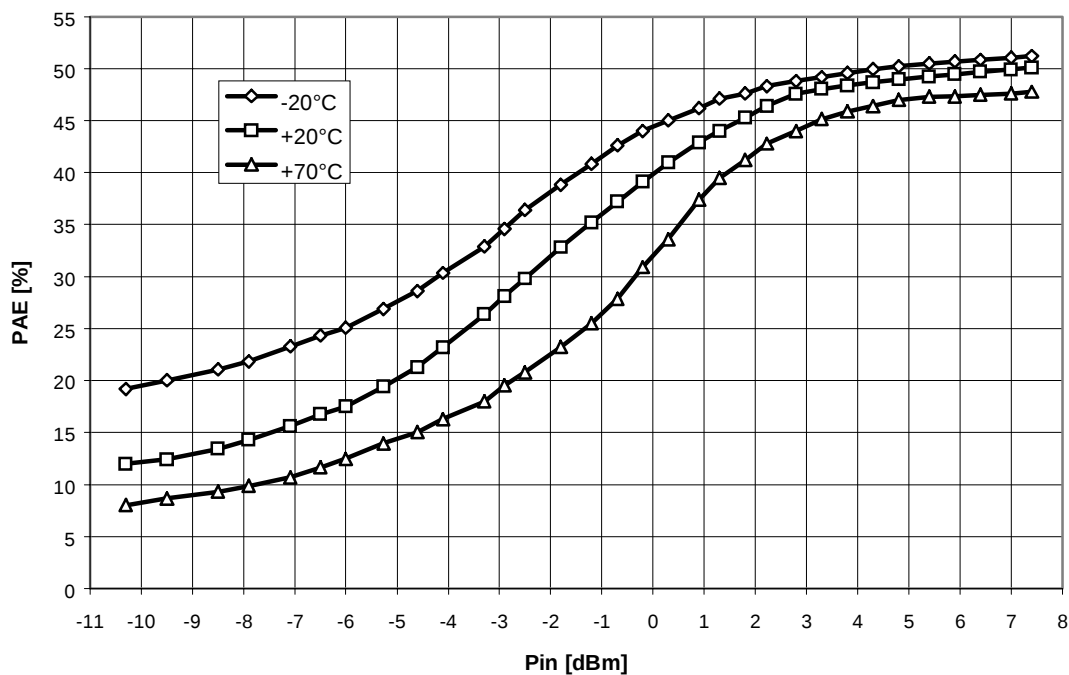
Output Power at different Temperatures

($V_d=3.5V$, $V_{control}=2.2V$, $f=900MHz$, duty cycle 12.5%, $t_{on}=577\mu s$)



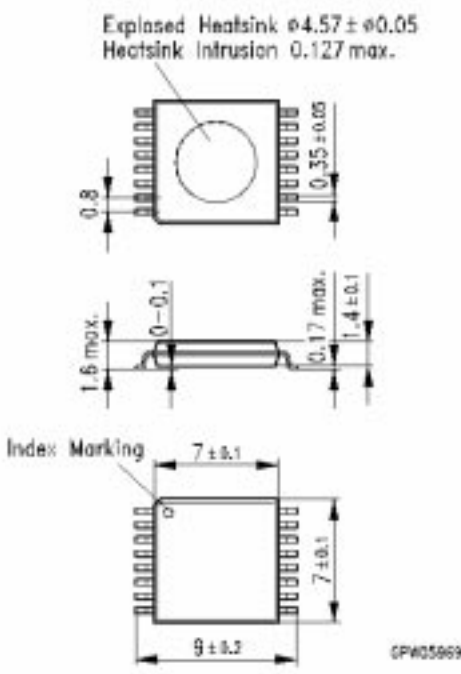
PAE at different Temperatures

($V_d=3.5V$, $V_{control}=2.2V$, $f=900MHz$, duty cycle 12.5%, $t_{on}=577\mu s$)



A detailed micrograph of the CGY96 amplifier chip. The chip is a yellow square with various pins and internal structures. Labels include: Vaux, CLK, Vcontrol, GND, IN, OUT, SIEMENS, GSM POWER, AMPLIFIER, CGY96, 10uH, 1n, 47n, 22p, 43nH, 12p, 3.3 OHM, VD, 1p, 10p, and 1n. The chip is mounted on a black substrate with various components and traces.

17.07.97

 Exploded Heatsink $\varnothing 4.57 \pm \varnothing 0.05$ Heatsink Intrusion 0.127 max. 0.8 0.35 ± 0.05 1.6 max. 0.1 0.17 max. 1.4 ± 0.1 Index Marking 7 ± 0.1 7 ± 0.1 8 ± 0.2 GPW05969	Published by Siemens AG, Bereich Bauelemente, Vertrieb, Produkt-Information, Balanstraße 73, D-81541 München Siemens AG 1996. All Rights Reserved As far as patents or other rights of third parties are concerned, liability is only assumed for components per se, not for applications, processes and circuits implemented within components or assemblies. The information describes the type of component and shall not be considered as assured characteristics. Terms of delivery and rights to change design reserved. For questions on technology, delivery and prices please contact the Offices of Semiconductor Group in Germany or the Siemens Companies and Representatives world-wide (see address list). Due to technical requirements components may contain dangerous substances. For information on the type in question please contact your nearest Siemens Office, Semiconductor Group. Siemens AG is an approved CECC manufacturer.
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